

Form 1449*	Atty. Docket No.: 303.355US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: <i>2314</i> <i>Unknown</i> <i>973</i> <i>09/09/88</i> <i>5795</i> <i>06/18/01</i>

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Examiner <i>Thierry Dauvin</i>	Date Considered <i>12/04/01</i>
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Form 1449*	Atty. Docket No.: 303.355US4	Serial No. Unknown 61183771
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
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				Class	Subclass	Yes
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Examiner

Theresa L. Parker

Date Considered

12/10/96

\*Substitute Disclosure Statement Form (PTO 1449)

\*\*EXAMINER: Initial if citation considered whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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12/14/96

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Date Considered

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*John D. Miller*

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Theresa S. Johnson

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